| Ref<br># | Hits    | Search Query   | DBs   | Default<br>Operator | Plurals | Time Stamp       |
|----------|---------|--|---|---------------------|---------|------------------|
| L1       | 0       | (insulated adj double adj gate adj<br>FET) or (insulated adj dual adj gate<br>adj FET)                     | US-PGPUB;<br>USPAT;<br>USOCR;<br>EPO; JPO;<br>DERWENT;<br>IBM_TDB | OR                  | ON      | 2005/09/16 12:24 |
| L2       | 955     | (double adj gate adj FET) or (dual adj<br>gate adj FET)  | US-PGPUB;<br>USPAT;<br>USOCR;<br>EPO; JPO;<br>DERWENT;<br>IBM_TDB | OR                  | ON      | 2005/09/16 12:08 |
| L3       | 1864806 | insulat\$4   | US-PGPUB;<br>USPAT;<br>USOCR;<br>EPO; JPO;<br>DERWENT;<br>IBM_TDB | OR                  | ON      | 2005/09/16 12:08 |
| L4       | 226     | 2 and 3  | US-PGPUB;<br>USPAT;<br>USOCR;<br>EPO; JPO;<br>DERWENT;<br>IBM_TDB | OR                  | ON      | 2005/09/16 12:08 |
| L5       | 5736015 | ((level adj shift\$4) or resist\$4 or diode or divid\$4)   | US-PGPUB;<br>USPAT;<br>USOCR;<br>EPO; JPO;<br>DERWENT;<br>IBM_TDB | OR                  | ON      | 2005/09/16 12:09 |
| L6       | 170     | 4 and 5  | US-PGPUB;<br>USPAT;<br>USOCR;<br>EPO; JPO;<br>DERWENT;<br>IBM_TDB | OR .                | ON      | 2005/09/16 12:24 |
| L7       | 4       | (insulated adj double adj gate adj<br>transistor\$1) or (insulated adj dual adj<br>gate adj transistor\$1) | US-PGPUB;<br>USPAT;<br>USOCR;<br>EPO; JPO;<br>DERWENT;<br>IBM_TDB | OR                  | ON      | 2005/09/16 12:37 |
| L8       | 1       | ("5689144").PN.  | USPAT   | OR                  | OFF     | 2005/09/16 12:27 |
| L9       | 1       | (insulated adj back adj gate)  | US-PGPUB;<br>USPAT;<br>USOCR;<br>EPO; JPO;<br>DERWENT;<br>IBM_TDB | OR                  | ON      | 2005/09/16 13:06 |

|     | 1     |   | <del> </del>  | I  |    |                  |
|-----|-------|---|---|----|----|------------------|
| L10 | 31405 | "same amplitude" or "same<br>magnitude"   | US-PGPUB;<br>USPAT;<br>USOCR;<br>EPO; JPO;<br>DERWENT;<br>IBM_TDB | OR | ON | 2005/09/16 13:07 |
| L11 | 28    | 10 and (2 or 7)   | US-PGPUB;<br>USPAT;<br>USOCR;<br>EPO; JPO;<br>DERWENT;<br>IBM_TDB | OR | ON | 2005/09/16 13:51 |
| L12 | 1165  | 327/427   | US-PGPUB;<br>USPAT;<br>USOCR;<br>EPO; JPO;<br>DERWENT;<br>IBM_TDB | OR | ON | 2005/09/16 13:51 |
| L13 | 41660 | (double or dual) SAME (transistor\$1 or FET\$1)   | US-PGPUB;<br>USPAT;<br>USOCR;<br>EPO; JPO;<br>DERWENT;<br>IBM_TDB | OR | ON | 2005/09/16 13:52 |
| L14 | 142   | 12 and 13   | US-PGPUB;<br>USPAT;<br>USOCR;<br>EPO; JPO;<br>DERWENT;<br>IBM_TDB | OR | ON | 2005/09/16 13:52 |
| L15 | 821   | 327/434   | US-PGPUB;<br>USPAT;<br>USOCR;<br>EPO; JPO;<br>DERWENT;<br>IBM_TDB | OR | ON | 2005/09/16 13:57 |
| L16 | 0     | ((insulated adj double adj gate adj<br>FET) SAME (change adj direction)<br>SAME amplitude SAME magnitude<br>SAME (level adj shift\$4)).clm. | US-PGPUB;<br>USPAT;<br>USOCR;<br>EPO; JPO;<br>DERWENT;<br>IBM_TDB | OR | ON | 2005/09/16 14:02 |
| L17 | 0     | ((insulated adj double adj gate adj<br>FET) SAME (change adj direction)<br>SAME amplitude SAME magnitude).<br>clm.                          | US-PGPUB;<br>USPAT;<br>USOCR;<br>EPO; JPO;<br>DERWENT;<br>IBM_TDB | OR | ON | 2005/09/16 14:02 |